Product data sheet

1. General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4350Z

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- · High collector current gain (hFE) at high IC
- · High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- DC/DC converters
- · Supply line switching
- Battery charger
- LED backlighting
- Linear voltage regulation (LDO)
- Driver in low supply voltage applications, e.g. lamps, LEDs
- · Inductive load driver (for example relays, buzzers, motors)

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|--------------------|---|--|-----|-----|-----|-----|------|
| V _{CEO} | collector-emitter voltage | open base | | - | - | -50 | V |
| I _C | collector current | | | - | - | -3 | Α |
| I _{CM} | peak collector current | single pulse; t _p ≤ 1 ms | | - | - | -5 | Α |
| R _{CEsat} | collector-emitter saturation resistance | I_C = -2 A; I_B = -200 mA; T_{amb} = 25 °C | [1] | - | 120 | 150 | mΩ |

[1] Pulsed test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$



50 V, 3 A PNP low VCEsat (BISS) transistor

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|----------------------------|----------------|
| 1 | В | base | 4 | C |
| 2 | С | collector | | В |
| 3 | Е | emitter | | , h |
| 4 | С | collector | ☐1 ☐2 ☐3 SC-73 (SOT223) | Ë sym132 |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|-------------|---------|---|---------|--|--|
| | Name | Description | Version | | |
| PBSS5350Z | SC-73 | plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body | SOT223 | | |

7. Marking

Table 4. Marking codes

| Тур | pe number | Marking code |
|-----|-----------|--------------|
| РΒ | SS5350Z | PB5350 |

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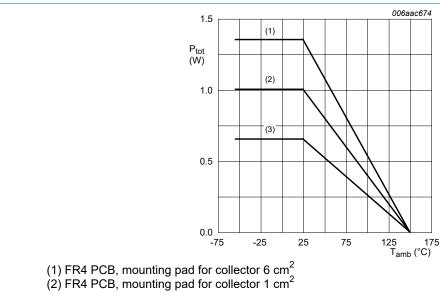
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|---------------------------|-------------------------------------|---------|-----|------|------|
| V _{CBO} | collector-base voltage | open emitter | | - | -60 | V |
| V _{CEO} | collector-emitter voltage | open base | | - | -50 | V |
| V _{EBO} | emitter-base voltage | open collector | | - | -6 | V |
| I _C | collector current | | | - | -3 | Α |
| I _{CM} | peak collector current | single pulse; t _p ≤ 1 ms | | - | -5 | Α |
| I _{BM} | peak base current | - | | - | -1 | Α |
| P _{tot} | total power dissipation | | [1] | - | 0.65 | W |
| | | | [2] | - | 1 | W |
| | | | [3] [4] | - | 1.35 | W |
| | | | [5] | - | 2 | W |
| Tj | junction temperature | | | - | 150 | °C |
| T _{amb} | ambient temperature | | | -65 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |

- Device mounted on an FR4 Printed-Circuit Board (PCB), 35 µm single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 1 cm². Device mounted on an FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 6 cm². [3]
- Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 1 cm² Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 6 cm².



- (3) FR4 PCB, standard footprint

Power derating curves Fig. 1.

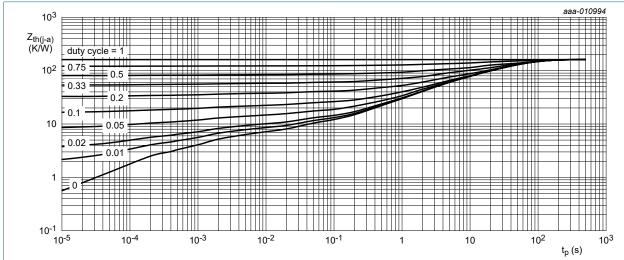
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9. Thermal characteristics

Table 6. Thermal characteristics

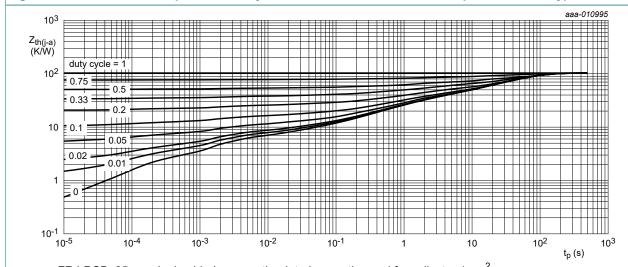
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|-------------|---------|-----|-----|------|------|
| $R_{th(j-a)}$ | thermal resistance from | in free air | [1] | - | - | 192 | K/W |
| | junction to ambient | [2] | - | - | 125 | K/W | |
| | | | [3] [4] | - | - | 92 | K/W |
| | | | [5] | - | - | 62.5 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | - | 16 | K/W |

- Device mounted on an FR4 PCB, 35 μm single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, 35 μm single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3]
- Device mounted on an FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 6 cm². Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 1 cm². [4]
- Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 6 cm². [5]



FR4 PCB, 35 µm single-sided copper, tin-plated and standard footprint.

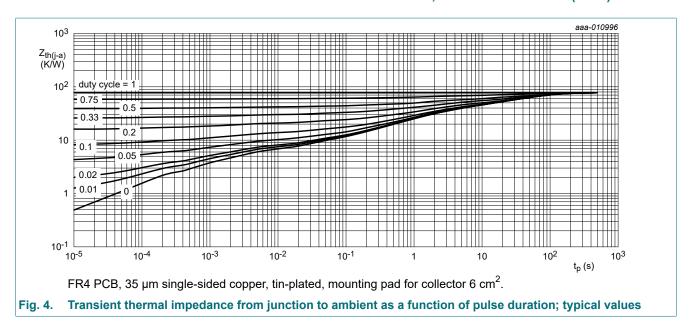
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 1 cm².

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|----------------------|---|---|-----|-----|-----|------|------|
| V _{(BR)CBO} | collector-base breakdown voltage | I _C = -100 μA; I _E = 0 A | | -60 | - | - | V |
| $V_{(BR)CEO}$ | collector-emitter breakdown voltage | $I_C = -10 \text{ mA}; I_B = 0 \text{ A}$ | | -50 | - | - | V |
| V _{(BR)EBO} | emitter-base breakdown voltage (collector open) | I _E = -100 μA; I _C = 0 A | | -6 | - | - | V |
| I _{CBO} | collector-base cut-off | V _{CB} = -50 V; I _E = 0 A | | - | - | -100 | nA |
| | current | V _{CB} = -50 V; I _E = 0 A; T _j = 150 °C | | - | - | -50 | μA |
| I _{EBO} | emitter-base cut-off current | V _{EB} = -5 V; I _C = 0 A | | - | - | -100 | nA |
| h _{FE} | DC current gain | V _{CE} = -2 V; I _C = -500 mA | | 200 | - | - | |
| | | V _{CE} = -2 V; I _C = -1 A | [1] | 200 | - | - | |
| | | V _{CE} = -2 V; I _C = -2 A | [1] | 100 | - | - | |
| V _{CEsat} | collector-emitter saturation voltage | I _C = -500 mA; I _B = -50 mA | | - | - | -100 | mV |
| | | I _C = -1 A; I _B = -50 mA | | - | - | -180 | mV |
| | | I _C = -2 A; I _B = -200 mA | [1] | - | - | -300 | mV |
| R _{CEsat} | collector-emitter saturation resistance | $I_C = -2 \text{ A}; I_B = -200 \text{ mA}; T_{amb} = 25 \text{ °C}$ | [1] | - | 120 | 150 | mΩ |
| V_{BEsat} | base-emitter saturation voltage | I _C = -2 A; I _B = -200 mA | [1] | - | - | -1.2 | V |
| V_{BEon} | base-emitter turn-on voltage | V _{CE} = -2 V; I _C = -1 A; T _{amb} = 25 °C | [1] | - | - | -1.1 | V |
| f _T | transition frequency | $V_{CE} = -5 \text{ V}; I_{C} = -100 \text{ mA}; f = 100 \text{ MHz}$ | | 100 | - | - | MHz |

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- 10³

- 104

I_C (mA)

- 10²

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------|-----------------------|--|-----|-----|-----|------|
| C _c | collector capacitance | $V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz | - | - | 40 | pF |

- 1.2

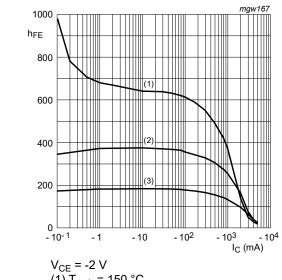
V_{BE} (V)

-0.8

- 1

- 10

[1] Pulsed test: $t_p \le 300 \,\mu s$; $\delta \le 0.02$



(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

- 10³

- 10²

- 10

- 10⁻¹

 $I_{\rm C}/I_{\rm B} = 10$

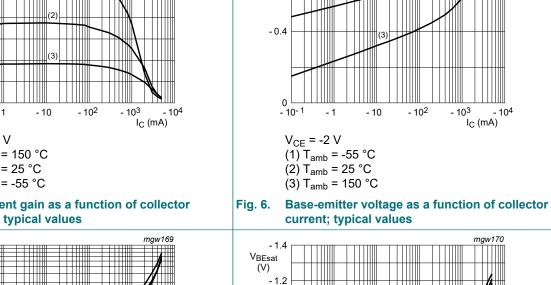
- 1

(1) $T_{amb} = 150 \, ^{\circ}C$ (2) T_{amb} = 25 °C (3) T_{amb} = -55 °C

V_{CEsat} (mV)

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 5. DC current gain as a function of collector current; typical values

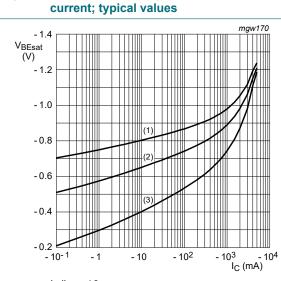


- 10³

- 10⁴

I_C (mA)

- 10²



$$I_{\rm C}/I_{\rm B} = 10$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

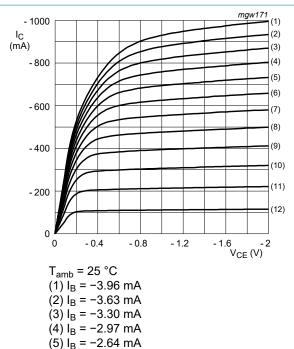
(2)
$$T_{amb} = 25 \, ^{\circ}C$$

Collector-emitter saturation voltage as a Fig. 7. function of collector current; typical values

- 10



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(6) $I_B = -2.31 \text{ mA}$ $(7) I_B = -1.98 \text{ mA}$

(8) $I_B = -1.65 \text{ mA}$

(9) $I_B = -1.32 \text{ mA}$

 $(10) I_B = -0.99 \text{ mA}$

 $(11) I_B = -0.66 \text{ mA}$

(12) $I_B = -0.33 \text{ mA}$

Fig. 9. Collector current as a function of collectoremitter voltage; typical values

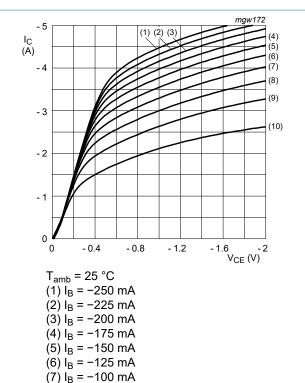
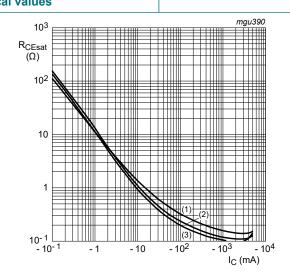


Fig. 10. Collector current as a function of collectoremitter voltage; typical values

 $(8) I_B = -75 \text{ mA}$

(9) $I_B = -50 \text{ mA}$

(10) $I_B = -25 \text{ mA}$



 $I_C/I_B = 20$

 $(1) T_{amb} = 150 °C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55$ °C

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

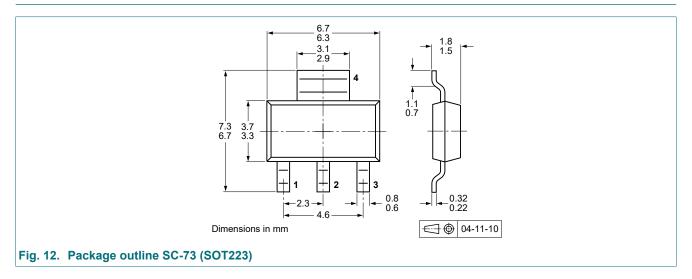
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11. Test information

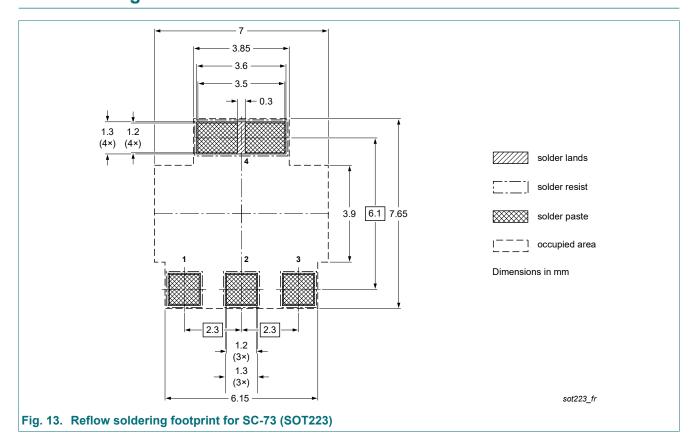
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline

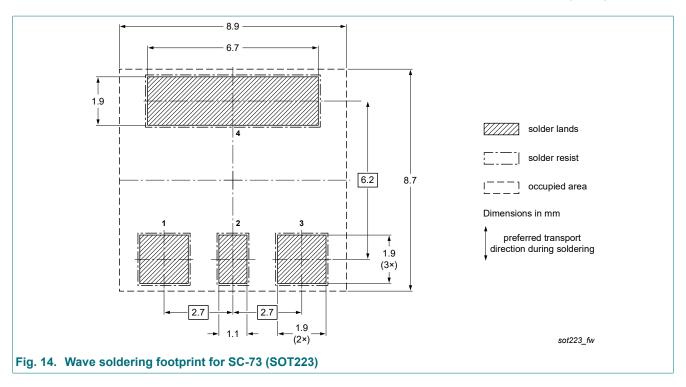


13. Soldering



PBSS53502

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14. Revision history

Table 8. Revision history

| Table of Notice in Motory | | | | | | |
|---------------------------|--------------|---|---------------|---------------|--|--|
| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes | | |
| PBSS5350Z v.5 | 20191118 | Product data sheet | - | PBSS5350Z v.4 | | |
| Modifications: | Nexperia. | this data sheet has been rede ve been adapted to the new o | | | | |
| PBSS5350Z v.4 | 20030513 | Product data sheet | - | PBSS5350Z v.3 | | |
| PBSS5350Z v.3 | 20030120 | Product data sheet | - | PBSS5350Z v.2 | | |
| PBSS5350Z v.2 | 20011113 | Product data sheet | - | PBSS5350Z v.1 | | |
| PBSS5350Z v.1 | 20010717 | Product data sheet | - | - | | |
| | | | | | | |

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15. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- Please consult the most recently issued document before initiating or completing a design.
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